TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

# SM10LZ47

## AC POWER CONTROL APPLICATIONS

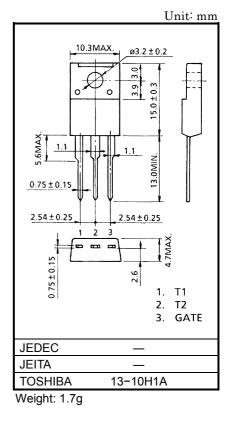
- Repetitive Peak Off-State Voltage : V<sub>DRM</sub> = 800V
- R.M.S. On–State Current : I<sub>T</sub> (RMS) = 10A
- High Commutation (dv / dt)
  - $: V_{ISOL} = 1500 V AC$

#### **MAXIMUM RATINGS**

Isolation Voltage

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CHARACTERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Off-State Voltage	V <sub>DRM</sub>	800	V	
R.M.S On-State Current (Full Sine Waveform)	I <sub>T (RMS)</sub>	10	А	
Peak One Cycle Surge On-State	ITOL	100 (50Hz)	A	
Current (Non-Repetitive)	ITSM	110 (60Hz)		
I <sup>2</sup> t Limit Value	l <sup>2</sup> t	50	A <sup>2</sup> s	
Critical Rate of Rise of On-State Current (Note)	di / dt	50	Α / μs	
Peak Gate Power Dissipation	P <sub>GM</sub>	5	W	
Average Gate Power Dissipation	P <sub>G (AV)</sub>	0.5	W	
Peak Gate Voltage	V <sub>FGM</sub>	10	V	
Peak Gate Current	I <sub>GM</sub>	2	А	
Junction Temperature	Tj	-40~125	°C	
Storage Temperature Range	T <sub>stg</sub>	-40~125	°C	
Isolation Voltage (AC, t = 1min.)	VISOL	1500	V	



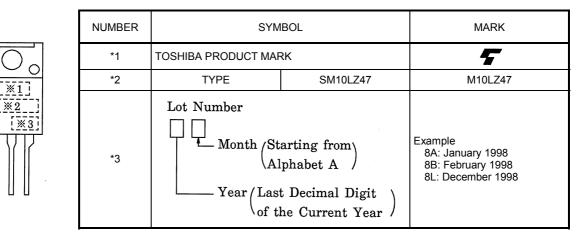
Note: di / dt test condition

 $V_{DRM}$  = 0.5 × Rated,  $I_{TM} \le 15A$ ,  $t_{gW} \ge 10\mu$ s,  $t_{gr} \le 250$ ns,  $i_{gp} = I_{GT} \times 2.0$ 

## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION		MIN	TYP.	MAX	UNIT
Repetitive Peak Off-State Current		I <sub>DRM</sub>	V <sub>DRM</sub> = Rated		_	_	20	μA
Gate Trigger Voltage	I	V <sub>GT</sub>	V <sub>D</sub> = 12V, R <sub>L</sub> = 20Ω	T2 (+) , Gate (+)		_	1.5	V
	П			T2 (+) , Gate (−)	_	-	1.5	
	Ш			T2 (-) , Gate (-)		_	1.5	
Gate Trigger Current	I	I <sub>GT</sub>	V <sub>D</sub> = 12V, R <sub>L</sub> = 20Ω	T2 (+) , Gate (+)		_	30	mA
	П			T2 (+) , Gate (−)		_	30	
	Ш			T2 (-) , Gate (-)		_	30	
Peak On-State Voltage		V <sub>TM</sub>	I <sub>TM</sub> = 15A			_	1.5	V
Gate Non-Trigger Voltage		V <sub>GD</sub>	V <sub>D</sub> = Rated, Tc = 125°C		0.2	_	_	V
Holding Current $I_{H}$ $V_{D}$ = 12V, $I_{TM}$ = 1A		= 1A		_	50	mA		
nermal Resistance R <sub>th (j-c)</sub> Junction to Case, AC			_	3.4	°C/W			
Critical Rate of Rise of Off-State Voltage dv / dt VDRN Expol		V <sub>DRM</sub> = 600V, T <sub>j</sub> = 125°C Exponential Rise		_	300	_	V / µs	
Critical Rate of Rise of Off-State Vo at Commutation	oltage	(dv / dt) c	V <sub>DRM</sub> = 400V, T <sub>j</sub> = 125°C (di / dt) c = - 5.5A / ms		10	_	_	V / µs

### MARKING



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